

Notice of References Cited	Application/Control No. 10/062,776	Applicant(s)/Patent Under Reexam Yoshiyuki et al	
	Examiner Savitri Mulpuri	Art Unit 2812	Page 1 of 1

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*		Document Number	Date	Name	Classification ²	
		Country Code-Number-Kind Code	MM-YYYY ¹			
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* A copy of this reference is not being furnished with this Office action. See MPEP § 707.05(a). ¹ Dates in MM-YYYY format are publication dates. ² Classifications may be U.S. or foreign.